CMKD6001

SURFACE MOUNT
ULTRAmini™
TRIPLE ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES

ULTRAmini™

SOT-363 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmini™ surface mount package, designed for switching applications requiring extremely low leakage.

MARKING CODE: K01

MAXIMUM RATINGS: (T_A=25°C)

	SYMBOL		UNITS
Continuous Reverse Voltage	V_R	75	V
Peak Repetitive Reverse Voltage	V_{RRM}	100	V
Continuous Forward Current	I_F	250	mA
Peak Repetitive Forward Current	I_{FRM}	500	mA
Forward Surge Current, tp=1 μsec.	I_{FSM}	4000	mA
Forward Surge Current, tp=1 sec.	I_{FSM}	1000	mA
Power Dissipation	P_D	250	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	500	°C/W

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

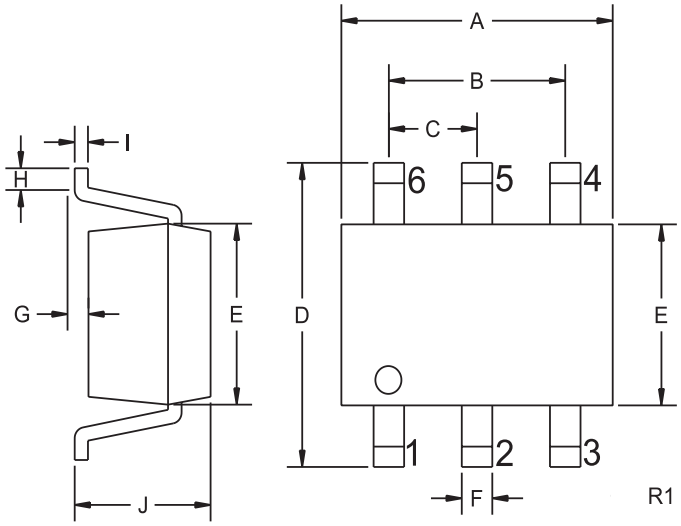
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	V_R=75V		500	pA
BV_R	I_R=100μA	100		V
V_F	I_F=1.0mA		0.85	V
V_F	I_F=10mA		0.95	V
V_F	I_F=100mA		1.1	V
C_T	V_R=0, f=1 MHz		2.0	pF
t_{rr}	I_R=I_F=10mA, R_L=100Ω Rec. to 1.0mA		3.0	μs

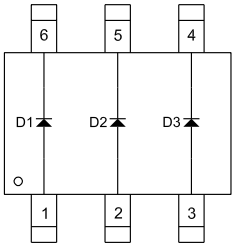
Central™
Semiconductor Corp.

CMKD6001

SURFACE MOUNT
ULTRAmini™
TRIPLE ISOLATED
LOW LEAKAGE SILICON
SWITCHING DIODES

SOT-363 CASE - MECHANICAL OUTLINE





DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A	0.073	0.085	1.85	2.15
B	0.051		1.30	
C	0.026		0.65	
D	0.075	0.091	1.90	2.30
E	0.043	0.055	1.10	1.40
F	0.006	0.012	0.15	0.30
G	0.000	0.004	0.00	0.10
H	0.010	-	0.25	-
I	0.004	0.010	0.10	0.25
J	0.031	0.039	0.80	1.00

SOT-363 (REV: R1)

LEAD CODE:

1) ANODE D1
2) ANODE D2
3) ANODE D3
4) CATHODE D3
5) CATHODE D2
6) CATHODE D1

MARKING CODE: K01

R2 (7-August 2003)